

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device has a current injection region (A) and current non-injection regions (B) located closer to respective laser beam-emitting end faces than the current injection region is. The semiconductor laser device has an oxide layer (106A) formed at a surface of a p-type $(\text{Al}_p\text{Ga}_{1-p})\text{In}_{1-q}\text{P}$ ($0 \leq p \leq x$, $0 \leq q \leq 1$) intermediate band gap layer (106) in each of the current non-injection regions (B), a p-type GaAs cap layer (107) formed on the intermediate band gap layer (106) in the current injection region (A), and a p-type GaAs contact layer (125) formed on the oxide layer (106A) and the p-type GaAs cap layer (107).